DISCRETE SEMICONDUCTORS

DATA SHEET

PEMH1; PUMH1 NPN/NPN resistor-equipped transistors; R1 = 22 kΩ, R2 = 22 kΩ

Product specification Supersedes data of 2001 Oct 22 2003 Oct 08





NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMH1; PUMH1

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	NPN	_	_	_
R1	bias resistor	22	_	kΩ
R2	bias resistor	22	_	kΩ

DESCRIPTION

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE	PACKAGE		MARKING CODE	NPN/PNP	PNP/PNP
NUMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMH1	SOT666		H2	PEMD2	PEMB1
PUMH1	SOT363	SC-88	H*2 ⁽¹⁾	PUMD2	PUMB1

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OLITHINE AND CVMDOL		PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION		
PEMH1	6 5 4	1	emitter TR1		
PUMH1		2	base TR1		
	R1 R2	3	collector TR2		
	TR2		emitter TR2		
	TR1 R2 R1	5	base TR2		
		6	collector TR1		
	1 2 3				
	Top view MHC650				
	MHC650				

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PEMH1; PUMH1

ORDERING INFORMATION

TYPE NUMBER		PACKAGE				
I TPE NUMBER	NAME	DESCRIPTION	VERSION			
PEMH1	_	plastic surface mounted package; 6 leads	SOT666			
PUMH1	_	plastic surface mounted package; 6 leads	SOT363			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
Io	output current (DC)		_	100	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device				•	•
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMH1; PUMH1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or		•	
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0$	_	_	1	μΑ
		V _{CE} = 30 V; I _B = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	180	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA	60	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100 \mu\text{A}; V_{CE} = 5 \text{V}$	_	1.1	0.8	V
V _{i(on)}	input-on voltage	$I_C = 5 \text{ mA}; V_{CE} = 0.3 \text{ V}$	2.5	1.7	_	V
R1	input resistor		15.4	22	28.6	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$			2.5	pF

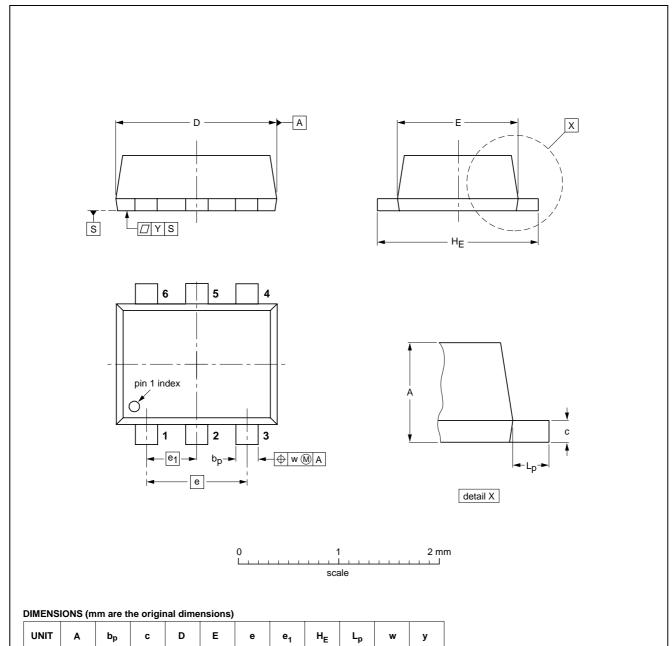
NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMH1; PUMH1

PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

0.1

0.5

2003 Oct 08 5

0.6

0.27

0.17

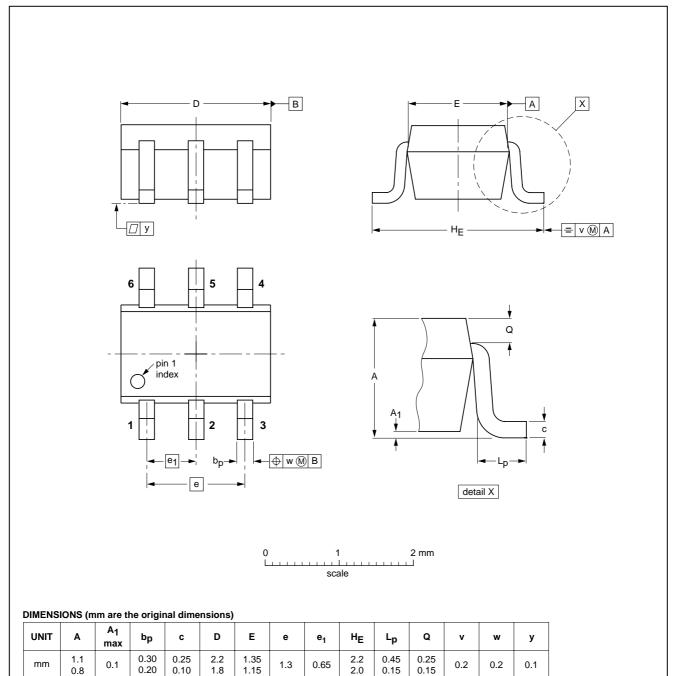
0.18

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMH1; PUMH1

Plastic surface mounted package; 6 leads

SOT363



OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMH1; PUMH1

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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